**Product Specification** 

# **Bipolar Memory Products**

### DESCRIPTION

The 82S321 is field programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The 82S321 is supplied with all outputs at a logical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

This device includes on-chip decoding and 2 chip enable inputs for ease of memory expansion. It features Three-state outputs for optimization of word expansion in bused organizations.

Ordering information can be found on the following page.

This device is also processed to military requirements for operation over the military temperature range. For specifications and ordering information consult the Signetics Military Data Book.

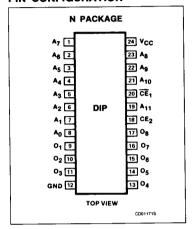
## **FEATURES**

- Address access time: 70ns max
- Power dissipation: 20μW/bit typ
- Input loading: −100µA max
- Two chip enable inputs
- · On-chip address decoding
- No separate fusing pins
- Unprogrammed outputs are Low level
- Fully TTL compatible
- Outputs: Three-state

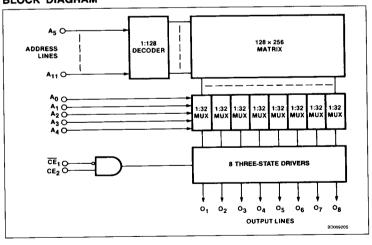
# **APPLICATIONS**

- Prototyping/volume production
- Sequential controllers
- Microprogramming
- Hardwired algorithms
- Control store
- Random logic
- Code conversion

#### PIN CONFIGURATION



# **BLOCK DIAGRAM**



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# 32K-Bit TL Bipolar PROM (4096 x 8)

82\$321

# ORDERING CODE

DESCRIPTION	ORDER CODES
Plastic Dual Inline 600mil wide 24-pin	N82S321 N

# **ABSOLUTE MAXIMUM RATINGS**

PARAMETER		RATING	UNIT	
V <sub>CC</sub>	Supply voltage	+7	V <sub>dc</sub>	
V <sub>IN</sub>	Input voltage	+5.5	V <sub>dc</sub>	
v <sub>o</sub>	Output voltage Off-state	+ 5.5	$V_{dc}$	
T <sub>A</sub> T <sub>STG</sub>	Temperature range Operating Storage	0 to +75 -65 to +150	°C	

# DC ELECTRICAL CHARACTERISTICS $0^{\circ}C \leqslant T_{A} \leqslant +75^{\circ}C$ , $4.75V \leqslant V_{CC} \leqslant 5.25V$

PARAMETER			LIMITS			
		TEST CONDITIONS <sup>1,2</sup>	Min	Typ <sup>5</sup>	Max	UNIT
V <sub>IL</sub>	Low				0.8	
V <sub>IH</sub>	High		2.0			V
V <sub>IC</sub>	Clamp	I <sub>IN</sub> = -12mA		-0.8	-1.2	
Output voltage		$\overline{CE}_1$ = Low, $CE_2$ = High				1
VoL	Low	I <sub>OUT</sub> = 9.6mA		İ	0.45	V
V <sub>OH</sub>	High	$I_{OUT} = -2mA$	2.4			
Input current						
կլ <u>.</u>	Low	V <sub>IN</sub> = 0.45V			-100	μΑ
l <sub>IH</sub>	High	V <sub>IN</sub> = 5.5V			40	
Output current						
loz	Hi-Z State	$\overline{CE}_1$ = High, $CE_2$ = Low, $V_{OUT}$ = 0.5			-40	μA
<b>02</b>		$\overline{CE}_1$ = High, $CE_2$ = Low, $V_{OUT}$ = 5.5		1	40	1
los	Short circuit <sup>3</sup>	$\overline{CE}_1 = Low, CE_2 = High, V_{OUT} = 0V$	-15		-70	mA
Supply current						
lcc		V <sub>CC</sub> = 5.25		130	175	mA
Capacitance						
		V <sub>CC</sub> = 5.0V				
C <sub>IN</sub>	Input	$V_{iN} = 2.0V$	į.	5	1	pF
C <sub>OUT</sub>	Output	V <sub>OUT</sub> = 2.0V	1	8		

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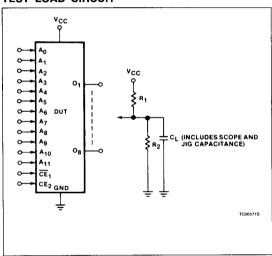
# AC ELECTRICAL CHARACTERISTICS $R_1 = 470\Omega$ , $R_2 = 1k\Omega$ , $C_1 = 30pF$ , $0^{\circ}C \le T_A \le +75^{\circ}C$ , $4.75V \le V_{CC} \le 5.25V$

PARAMETER		FROM		LIMITS		
	то		Min	Typ <sup>5</sup>	Max	UNIT
Access time <sup>4</sup>						
TAA	Output	Address		60	70	ns
TCE	Output	Chip enable		20	25	
Disable time <sup>6</sup>						
T <sub>CD</sub>	Output	Chip disable		20	25	ns

#### NOTES:

- 1. Positive current is defined as into the terminal referenced.
- 2. All voltages with respect to network ground.
- 3. Duration of short circuit should not exceed 1 second
- 4. Tested at an address cycle time of  $1\mu sec.$
- 5. Typical values are at  $V_{CC} = 5V$ ,  $T_A = 25$ °C.
- 6. Measured at a delta of 0.5V from Logic Level with R<sub>1</sub> = 750 $\Omega$ , R<sub>2</sub> = 750 $\Omega$  and C<sub>L</sub> = 5pF.

### **TEST LOAD CIRCUIT**



# **VOLTAGE WAVEFORM**

